

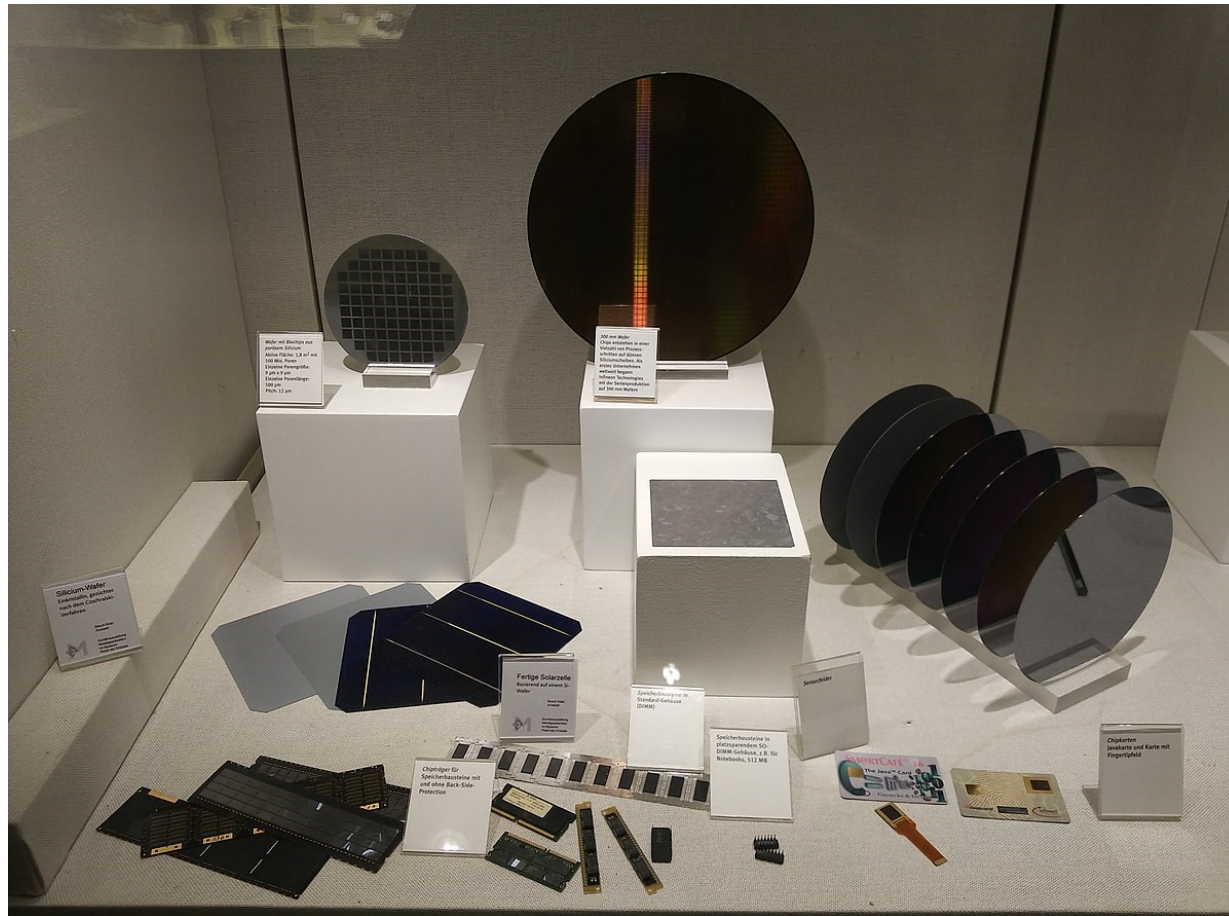
Corso «Fondamenti di Fisica delle Superfici»

Dr. Alberto Verdini

CNR-IOM

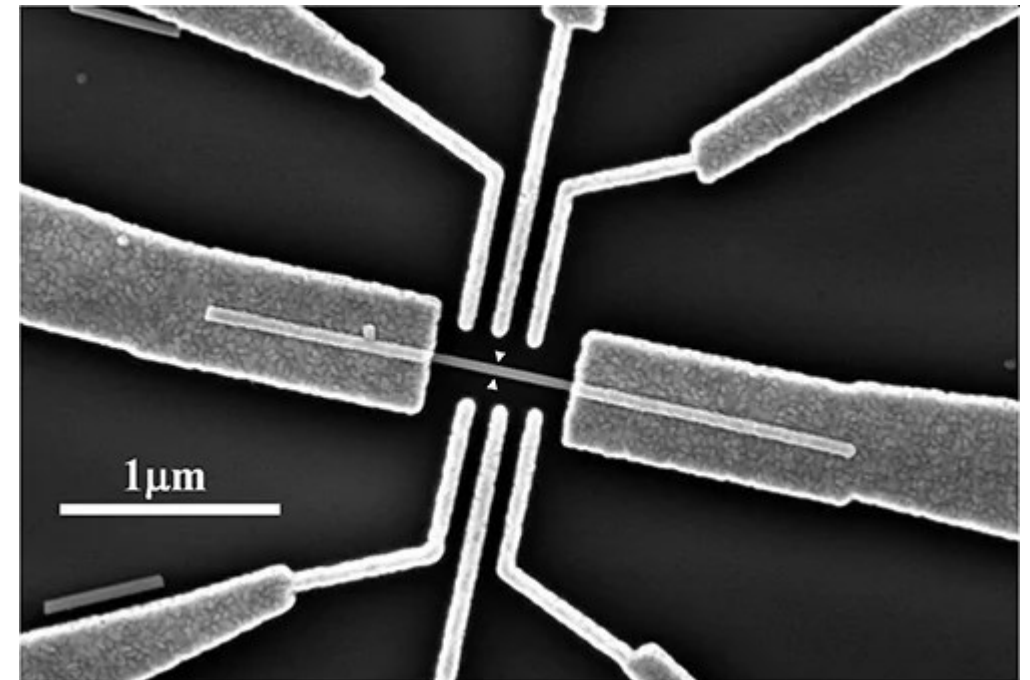
verdini@iom.cnr.it

Perché studiare le superfici?



Wafer di Silicio – tecnologia anni '60

Transistor



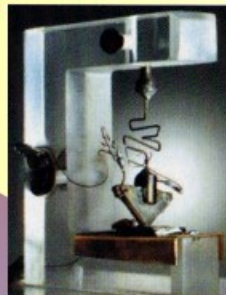


Gordon Moore's law: device downsizing (1965)

The number of transistor that can be placed inexpensively on a chip doubles every two years on average.

10^8 nm

**First solid state device
silicon transistor**
Texas Instruments
introduced the first Si
transistor in 1954

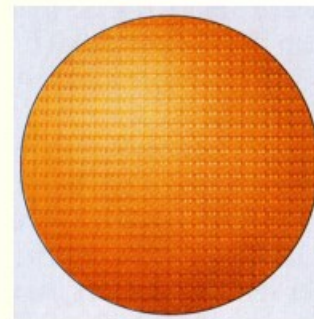


Size matters

Transistors in the
first microprocessor
(the Intel 4004)
measured 10 μ m.

Small talk

The transistors in Intel's
Pentium 4 were
constructed with processes
at 90 nm.



10^7 nm

10^6 nm

10^5 nm

10^4 nm

10^3 nm

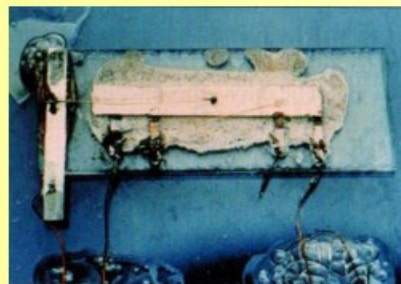
100 nm

10 nm

**Vacuum tube
(thermoionic valve)**
The first active
electronic device



**The first integrated
circuit**
Jack Kilby developed
the first integrated
circuit in 1958.



How low can we go?
Further downsizing
may not prove to be
economically viable

The smallest transistor that may be manufactured cost effectively is 9 nm

Limit of current manufacturing techniques is about 5 nm

Fundamental physical limit is just below 1 nm

New technologies, such as spintronics, will be needed to go below these limits

1900

1950

1960

1970

1980

1990

2000

2010

2020

Our World
in Data

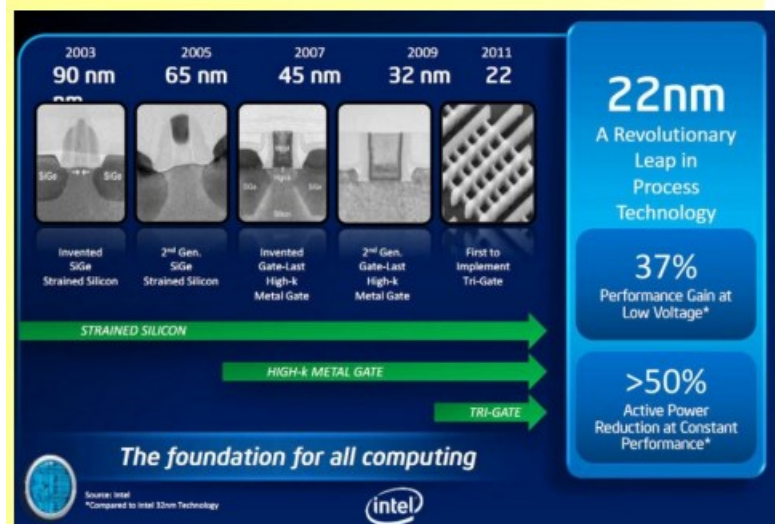
The chart illustrates the exponential growth of transistor counts in integrated circuits over time. The y-axis represents the transistor count on a logarithmic scale, ranging from 1,000 to 50,000,000,000. The x-axis represents the year, from 1970 to 2018. The data points are labeled with various processor models and their core counts, showing a clear upward trend.

Key data points include:

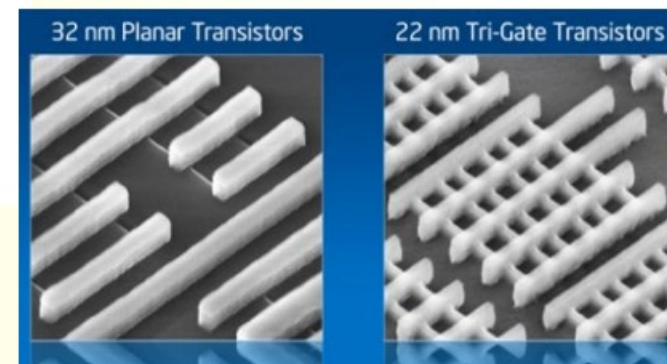
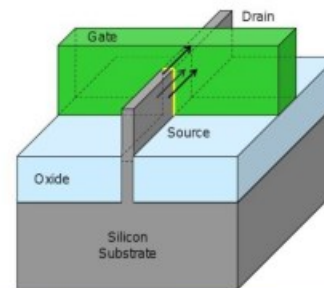
- Intel 4004 (1971)
- Intel 8008 (1972)
- Intel 8080 (1974)
- Intel 8085 (1976)
- Intel 8088 (1982)
- Intel 80286 (1985)
- Intel 80386 (1985)
- Intel 80486 (1989)
- Intel Pentium (1993)
- Intel Pentium Pro (1995)
- Intel Pentium 4 Prescott (2002)
- Intel Core 2 Duo (2006)
- Intel Core i7 (2008)
- Intel Core i9 (2017)
- Apple A7 (2012)
- Apple A12X Bionic (2017)
- Qualcomm Snapdragon 8cx (2018)
- ARM Cortex-A9 (2008)
- ARM Cortex-A53 (2015)
- ARM Cortex-A72 (2016)
- ARM Cortex-A76 (2018)

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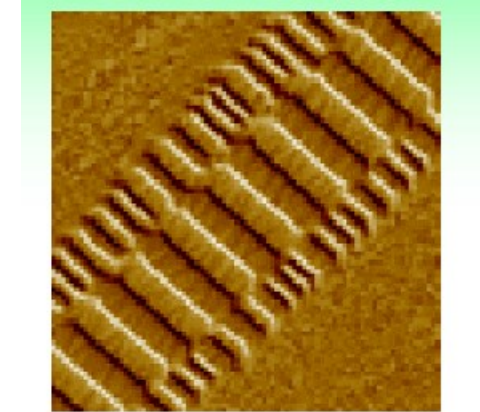
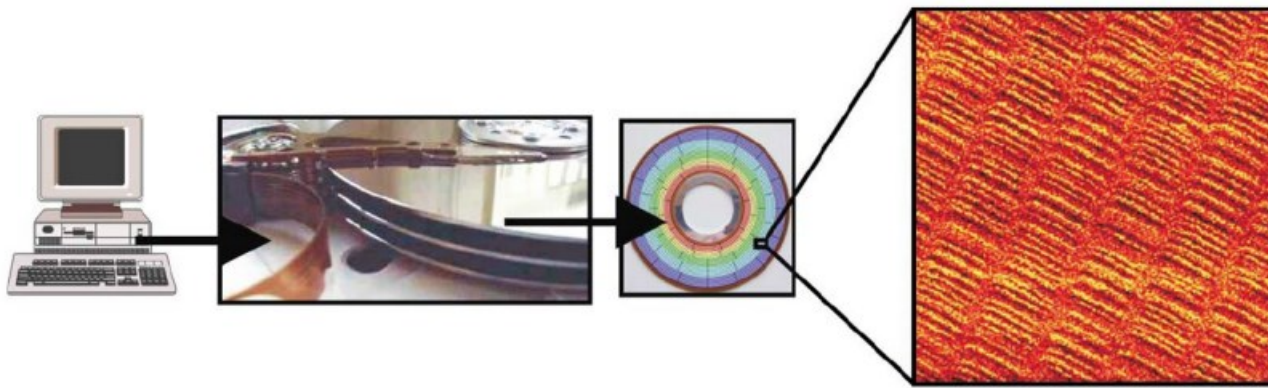
Legge di Moore:
Il numero di transistor nelle
CPU raddoppia ogni due anni



22 nm Tri-Gate Transistor

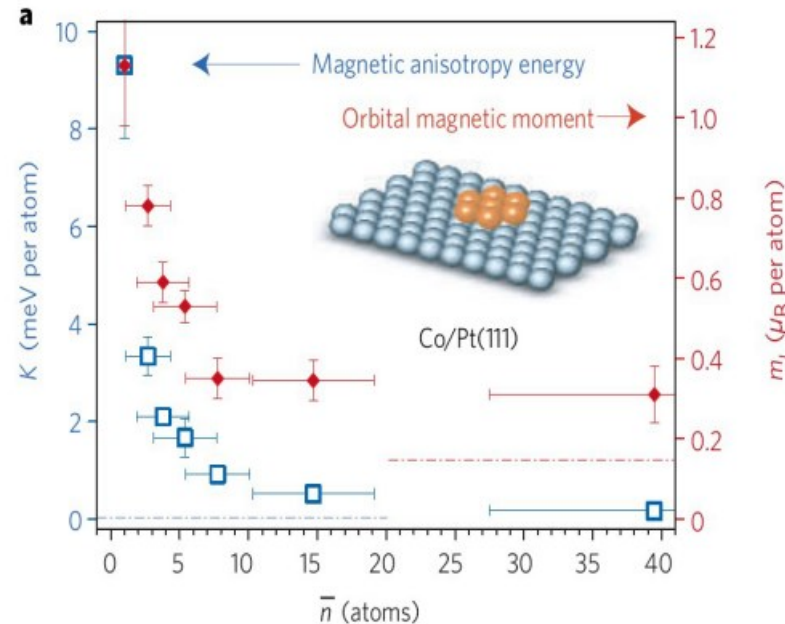


Perché studiare le superfici?



Magnetic hard drive
(25 μm x 25 μm).
Wires are about 2000
atoms wide.

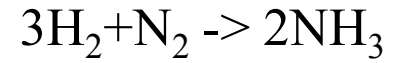
Data Storage Magnetico



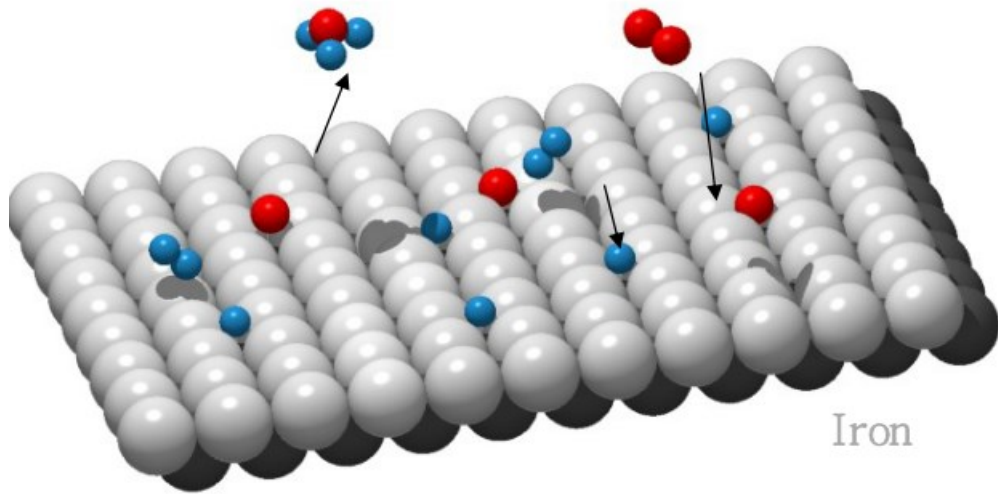
->Spintronica

Perché studiare le superfici?

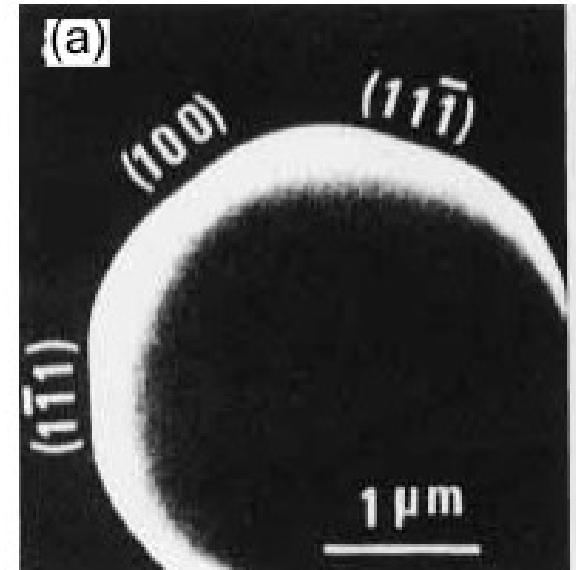
Processo Haber-Bosch (1910)



Catalisi eterogenea

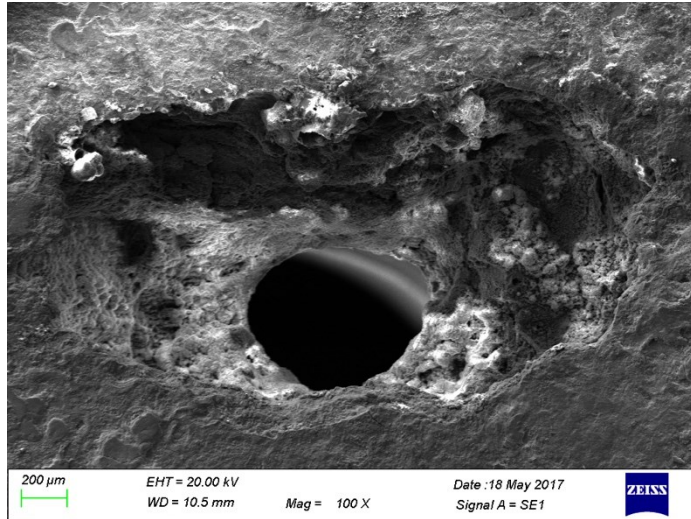


Processo utile per fertilizzanti
usato ancora oggi mediante superfici di Fe

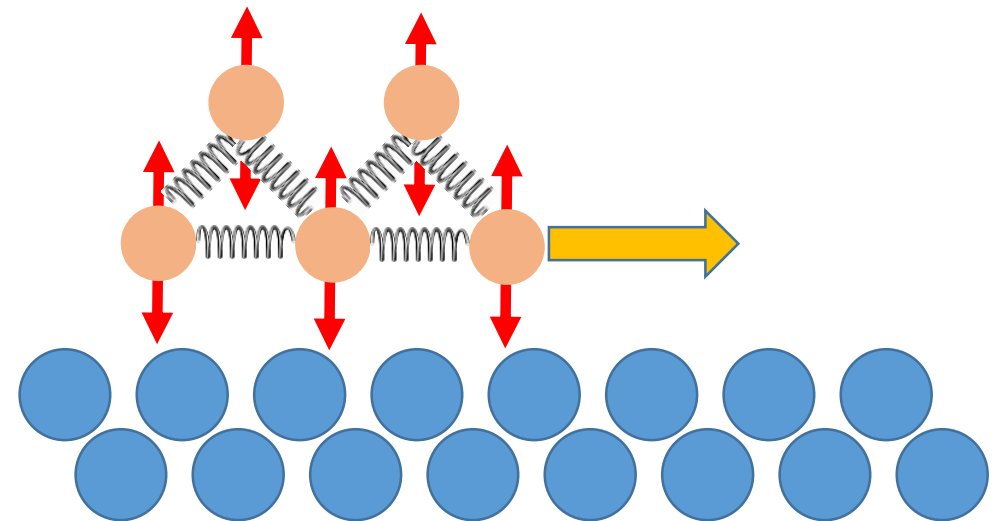
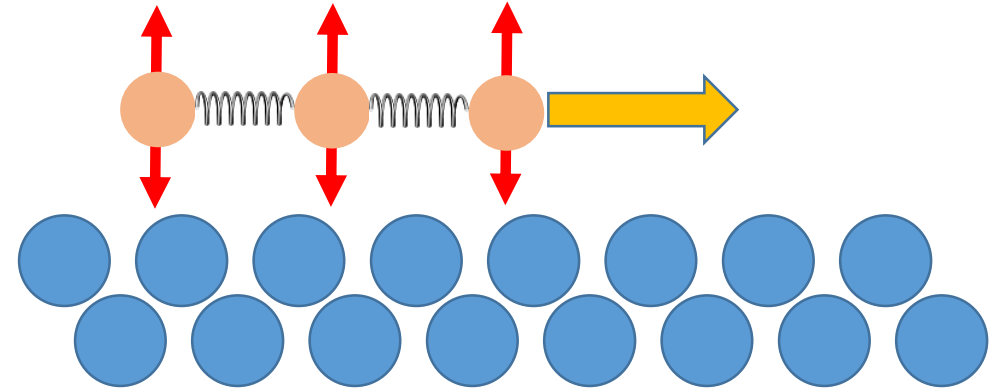


Perché studiare le superfici?

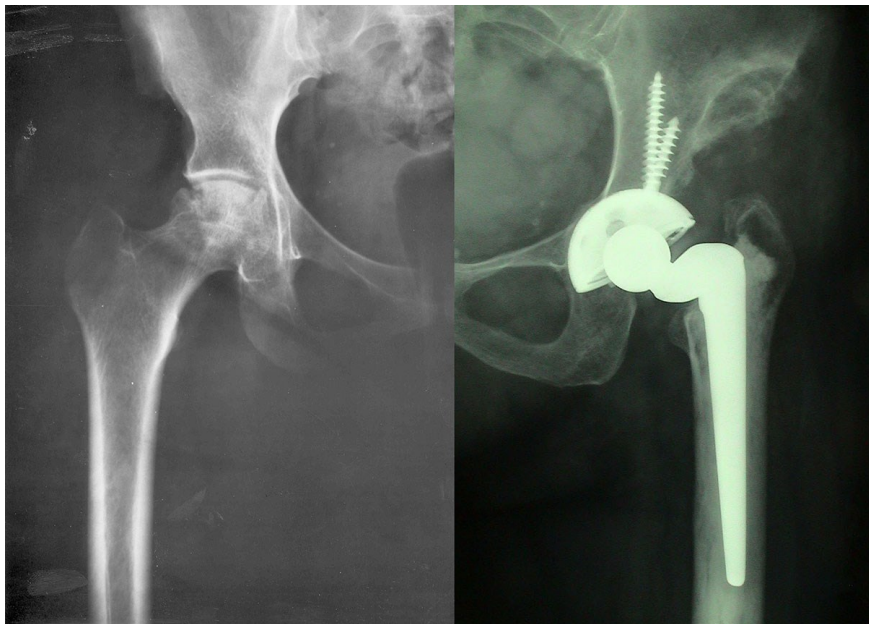
Corrosione



Attrito, adesione, Tribologia



Perché studiare le superfici?



Scienza dei materiali

Medicina

Rivestimento di materiali avanzati in protesi (composizione (metalli/polimeri/ceramica), attrito, rugosità, tasso di usura, resistenza ai graffi, durezza, biocompatibilità, ecc.)

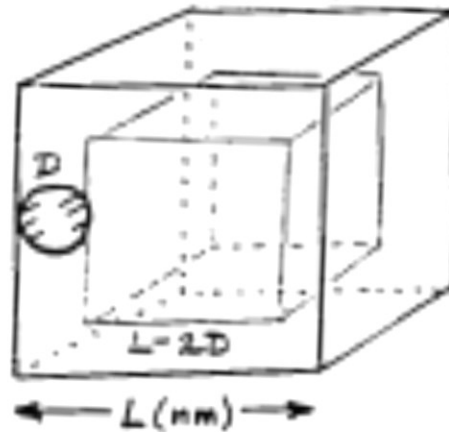
There's Plenty of Room at the Bottom è il titolo di una presentazione di Richard Feynmann alla riunione dell'APS al Caltech il 29 dicembre 1959.



NANOTECHNOLOGIES !

Perché studiare le superfici?

FRACTION OF ATOMS ON THE SURFACE
OF A CUBE: $D = \text{ATOMIC DIAM.} \approx 0.2 \text{ nm} = 2 \text{ \AA}$

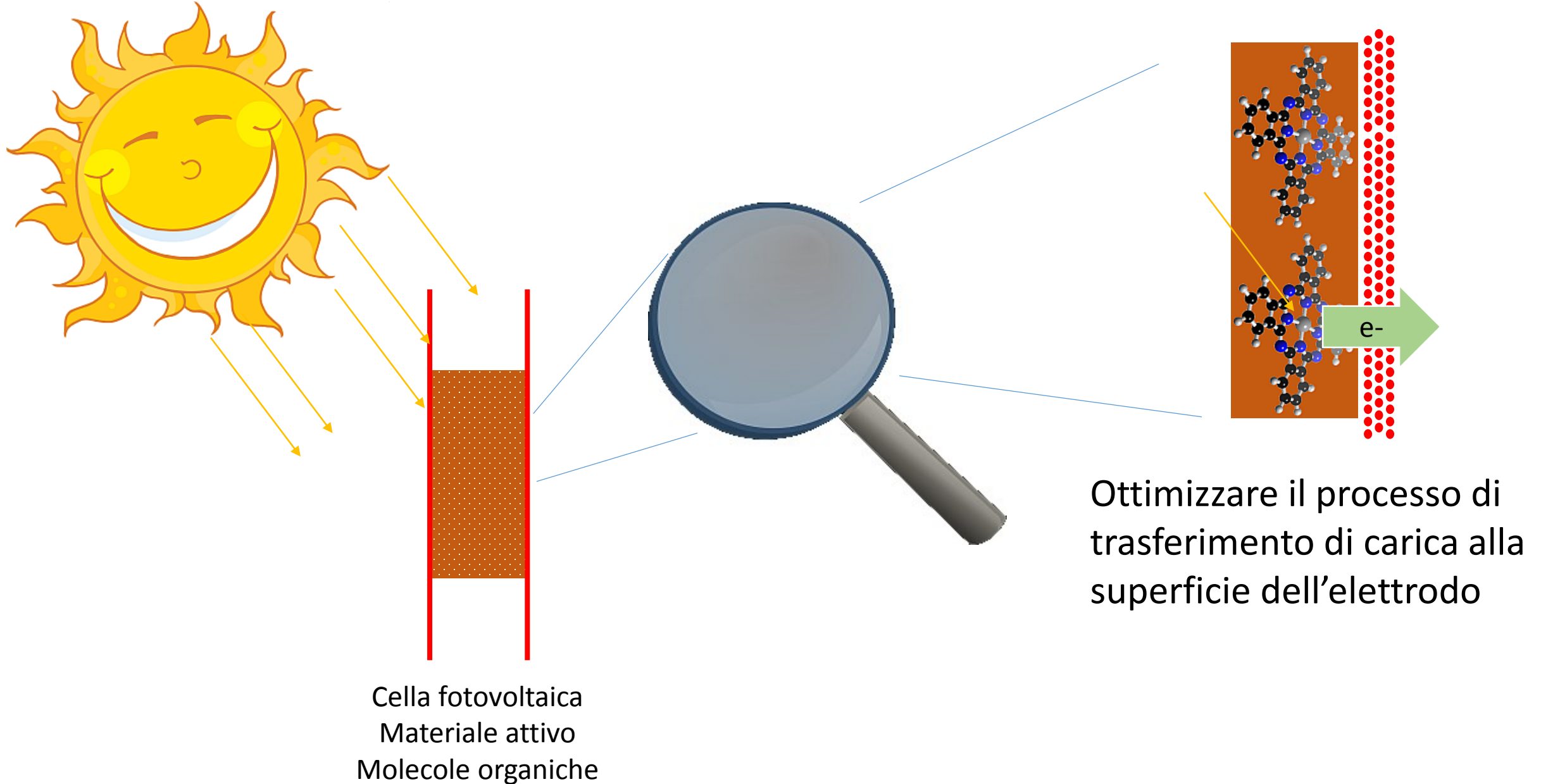


$$\text{SURFACE FRACTION} = \frac{L^3 - (L - 2D)^3}{L^3}$$

<u>L</u>	<u>FRACTION</u>
$1 \mu\text{m} = 1000 \text{ nm}$	$0.001 \approx 0.1\%$
$0.1 \mu\text{m} = 100 \text{ nm}$	$0.012 \approx 1.2\%$
$0.01 \mu\text{m} = 10 \text{ nm}$	$0.115 \approx 11.5\%$
$0.001 \mu\text{m} = 1 \text{ nm}$	$0.784 \approx 78.4\%$

NANOTECHNOLOGIES!

Perché studiare le superfici?



Fisica delle Superfici e sistemi modello

- Le superfici reali sono molto complesse e mal definite: policristalli, disordine, difetti,
- Dipendono dall'ambiente in cui si trovano
- Impurezze

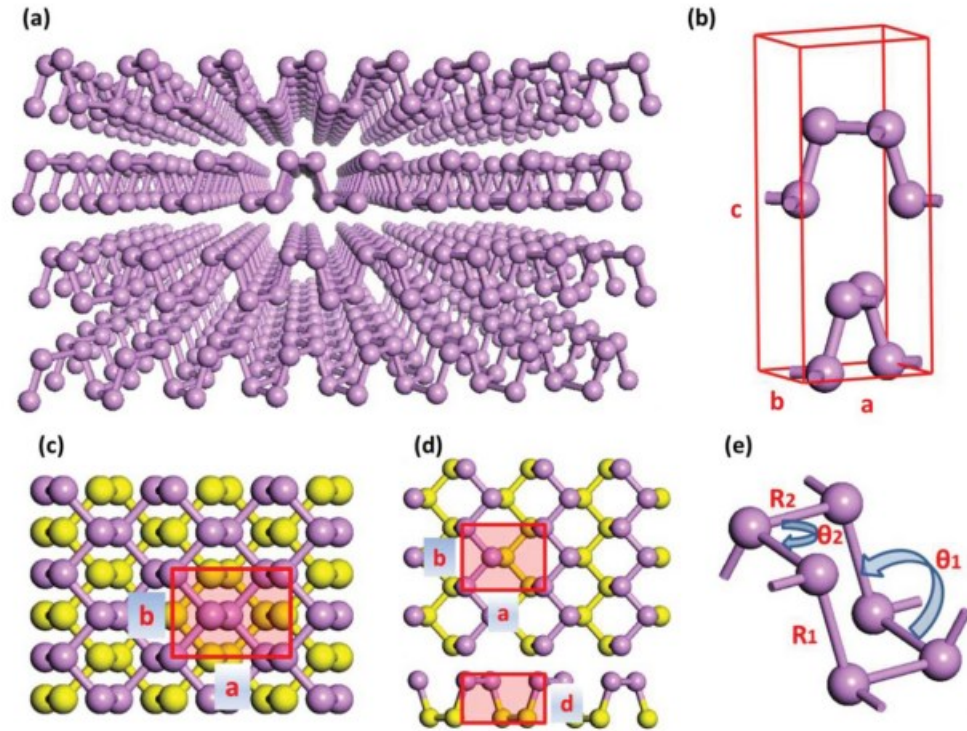
Come studiarle?

- Partire da sistemi semplici (UHV)
- Studiare le superfici a «basso indice» di cristalli singoli
- Capire bene queste superfici “ideali” e poi introdurre difetti/irregolarità/disordine in modo controllato
- Rendere i sistemi gradualmente più complessi nella speranza di avere modelli sempre più vicini alla realtà

Materiali 2D

- Graphene -> Nobel
- Altri sistemi monostrato? Silicene, Germanene, Stanene
- Borophene and Phosphorene

Black Phosphorous



PHYSICAL REVIEW B **93**, 035448 (2016)

Surface structure determination of black phosphorus using photoelectron diffraction

Luis Henrique de Lima,^{1,*} Lucas Barreto,^{1,2} Richard Landers,¹ and Abner de Siervo^{1,†}

¹Instituto de Física Gleb Wataghin, Universidade Estadual de Campinas, Campinas 13083-859, São Paulo, Brazil

²Centro de Ciências Naturais e Humanas, Universidade Federal do ABC, Santo André 09210-580, São Paulo, Brazil

(Received 16 November 2015; revised manuscript received 11 January 2016; published 26 January 2016)

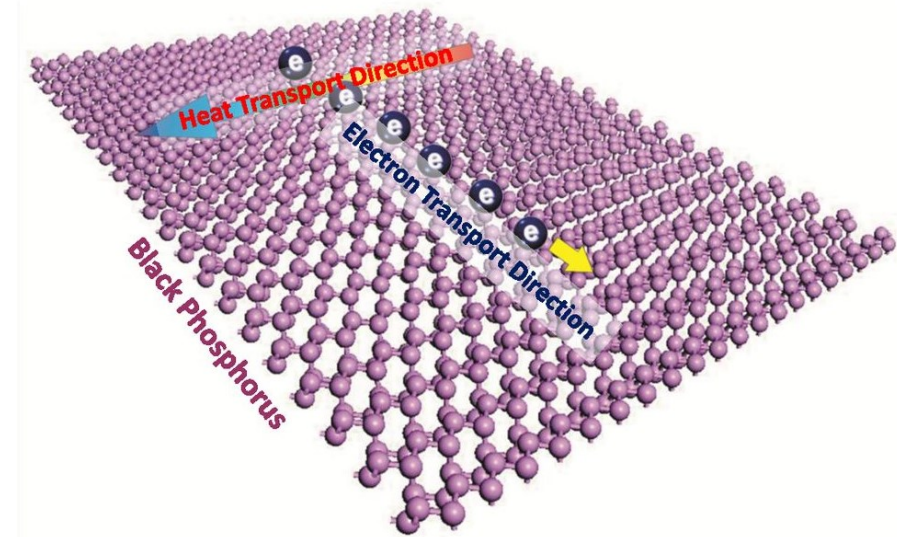
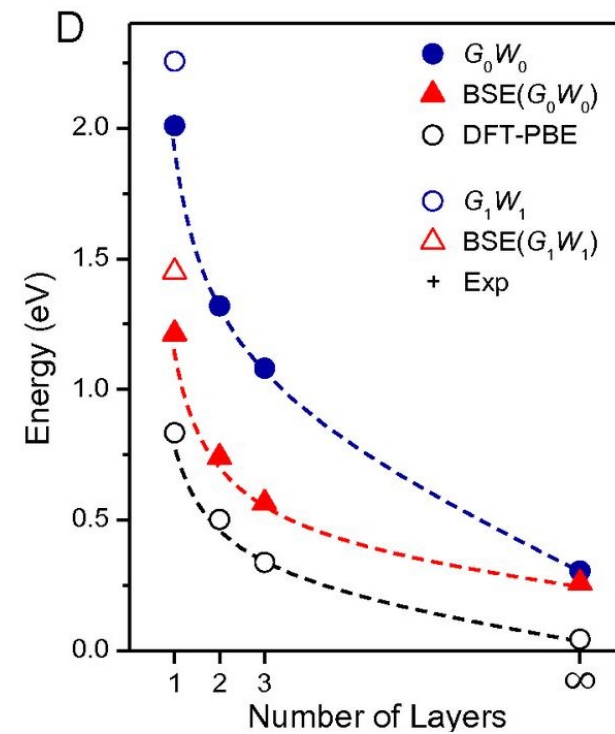
Applicazioni

- Transistor FET
- Dispositivi Optoelettronici
- Celle solari
- Scissione fotocatalitica dell'acqua
- Batterie Li-ion
- Materiali termoelettrici
- Sensori

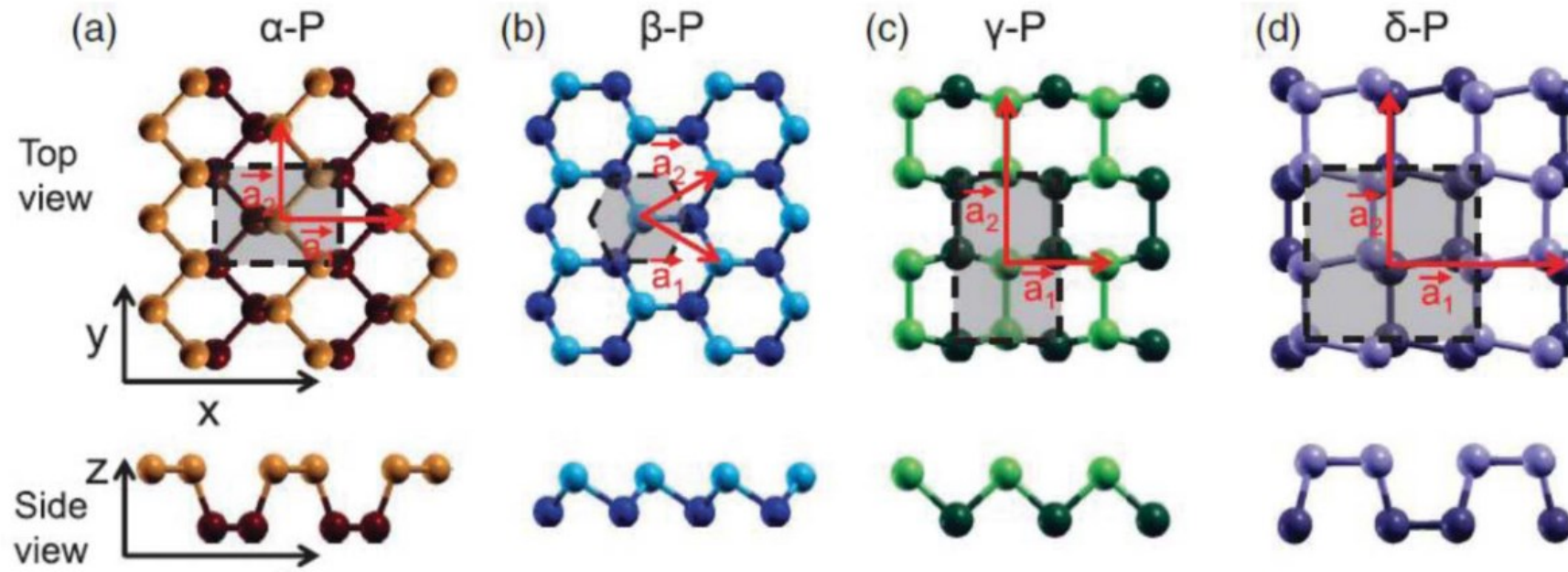
V. Sorkin et al. Critical Reviews in Solid State and Materials Sciences, 42, 1 (2016)

Black phosphorous principali proprietà interessanti:

- La gap dipende dal numero di strati
- Anisotropia sul piano del trasporto di calore e di elettroni



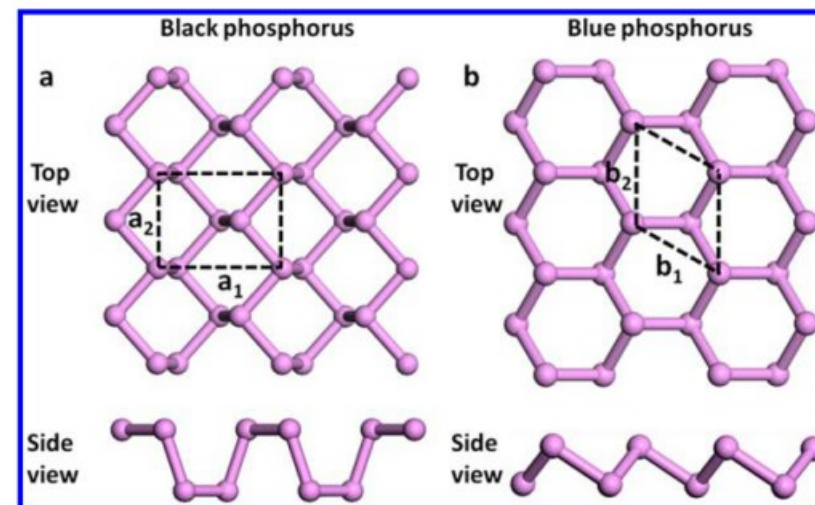
Molti possibili monostrati con diverse strutture



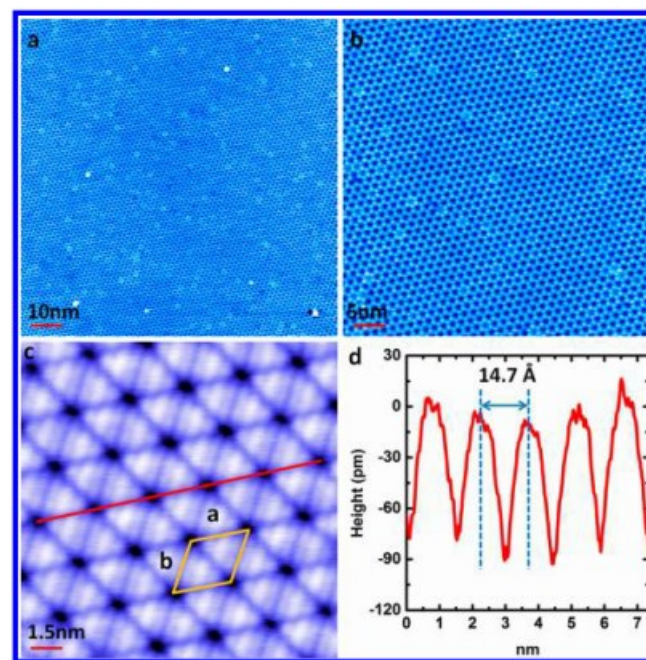
Fasi calcolate per un singolo strato di P

Epitaxial Growth of Single Layer Blue Phosphorus: A New Phase of Two-Dimensional Phosphorus

Jia Lin Zhang,^{†,‡} Songtao Zhao,[§] Cheng Han,^{†,‡,||} Zhunzhun Wang,^{§,⊥} Shu Zhong,[†] Shuo Sun,[‡] Rui Guo,[†] Xiong Zhou,[†] Cheng Ding Gu,[†] Kai Di Yuan,[‡] Zhenyu Li,^{*,§} and Wei Chen^{*,†,‡,||,#}



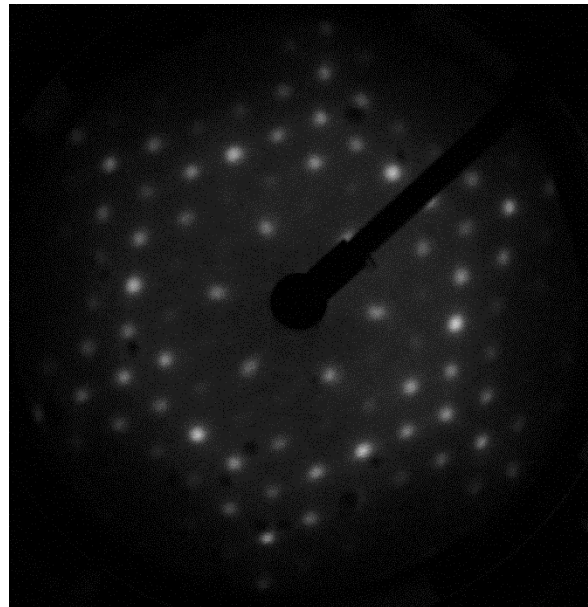
Blue Phosphorene/Au(111)



Perché non usare il fosforo rosso (molto molto economico) invece di quello nero (molto costoso)?

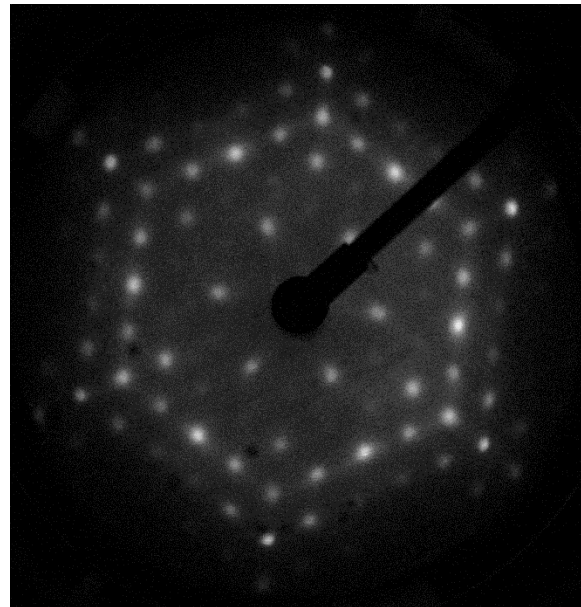
Red phosphorus

60 eV

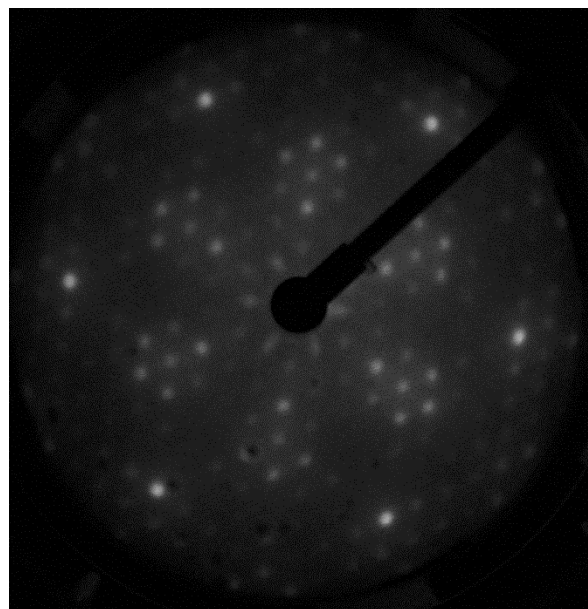


Black phosphorus

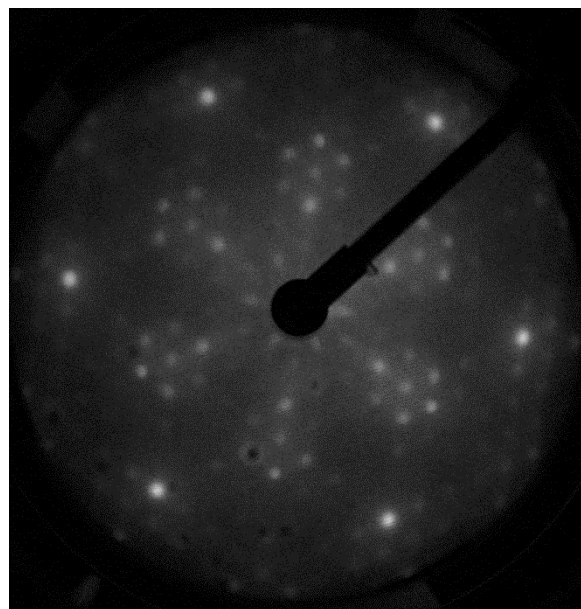
60 eV



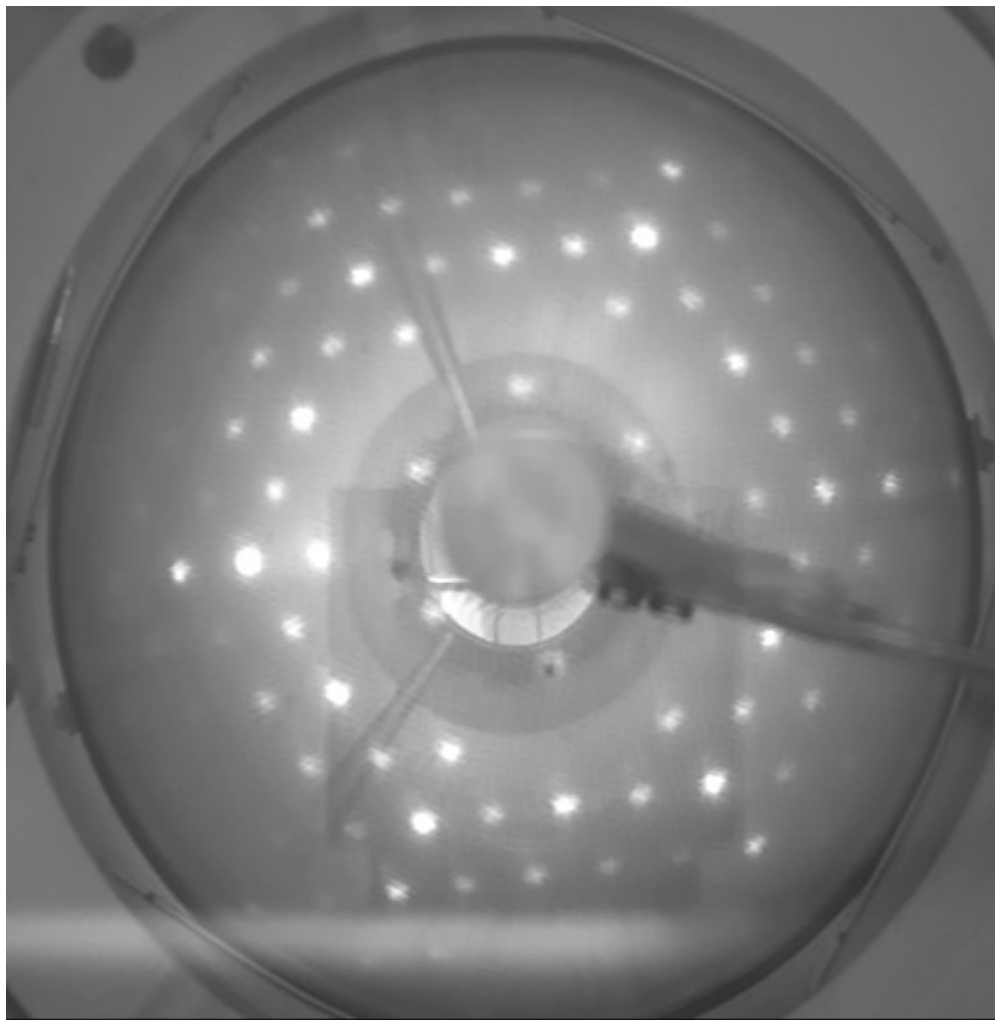
120 eV



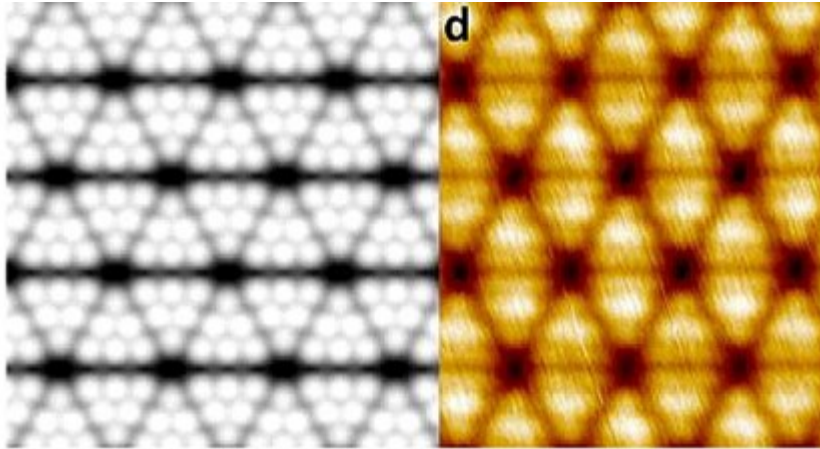
120 eV



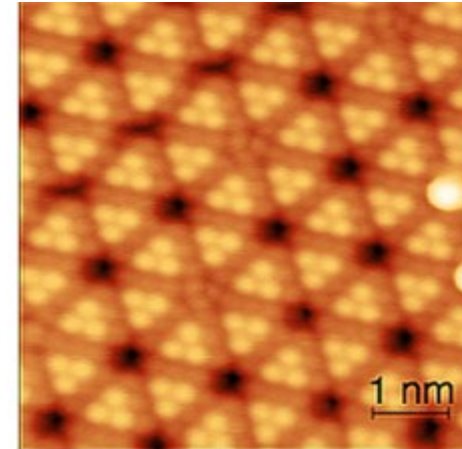
LEED measurements for Red (Left) and Black (Right) Phosphorous deposited on Au(111) in the VISIP lab of University of Trieste. Paper in preparation



$E_k = 66 \text{ eV}$



STM image of Black
Phosphorous/Au(111) from J.L. Zhang et
al. Nano Lett. 16, 4903 (2016)



STM image of Red
Phosphorous/Au(111)
taken in the STM lab
of TASC-IOM-CNR
in Trieste

- Diffrazione di raggi X da superfici (SXRD) per controllare il modello
- beamline SIXS a Soleil (Parigi, Francia) a luglio

